	No.1881A	<h1 style="margin: 0;">DRA03T</h1> <p style="margin: 0;">Silicon Planar Type</p> <h2 style="margin: 0;">0.3A Reverse Blocking Thyristor</h2>
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**Features**

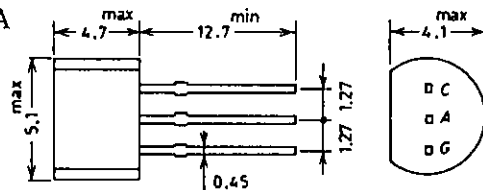
- Low-power switching and control
- Small size and light weight
- Peak OFF-state (reverse) voltage : - 100 to - 600V
- Average ON-state current : 0.3A
- TO92 package

Absolute Maximum Ratings at Ta = 25°C			DRA03TB	DRA03TC	DRA03TE	DRA03TG	unit
Repetitive Peak OFF-State Voltage	$V_{DRM}$	$R_{GK} = 1\Omega$	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	$R_{GK} = 1\Omega$	-150	-300	-500	-720	V
Repetitive Peak Reverse Voltage	$V_{RRM}$	$R_{GK} = 1\Omega$	-100	-200	-400	-600	V
Average ON-State Current	$I_{T(AV)}$	Ta = 30°C, single-phase half-wave	→	→	→	0.3	A
RMS ON-State Current	$I_{T(RMS)}$		→	→	→	0.45	A
Surge ON-State Current	$I_{TSM}$	Sine half-wave 1 cycle, 50Hz	→	→	→	9	A
Amperes Squared-Seconds	$\int i^2 T \cdot dt$	1ms ≤ t ≤ 10ms	→	→	→	0.4	A <sup>2</sup> S
Peak Gate Power Dissipation	$P_{GM}$	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.1	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	→	0.01	W
Peak Gate Forward Current	$I_{FGM}$	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.125	A
Peak Gate Forward Voltage	$V_{FGM}$	f ≥ 50Hz, duty ≤ 10%	→	→	→	3.5	V
Peak Gate Reverse Voltage	$V_{RGM}$		→	→	→	-5	V
Junction Temperature	Tj		→	→	→	110	°C
Storage Temperature	Tstg		→	→	→	-40 to +125	°C
Weight			→	→	→	0.2	g

**Electrical Characteristics at Ta = 25°C**

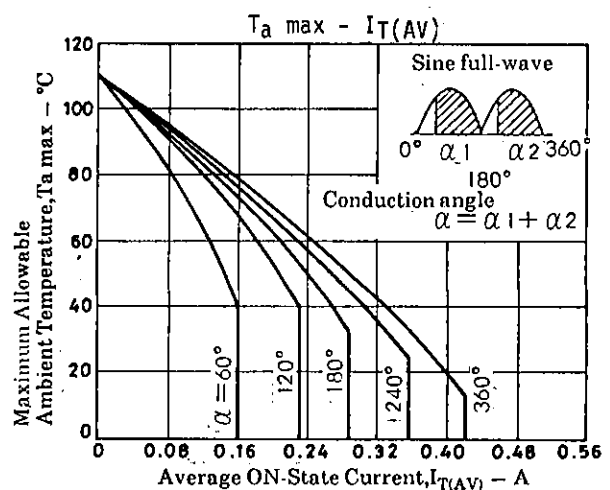
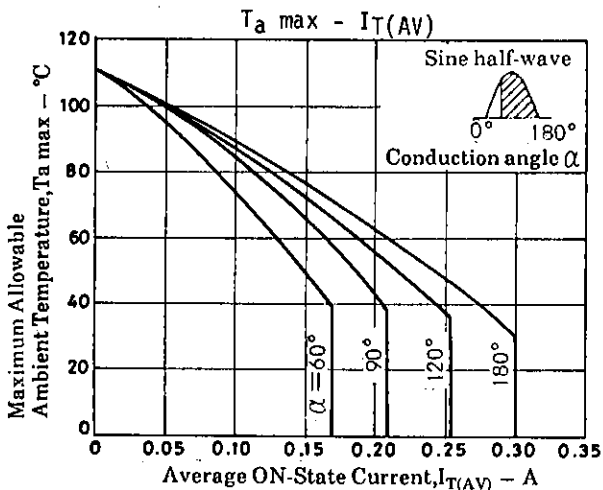
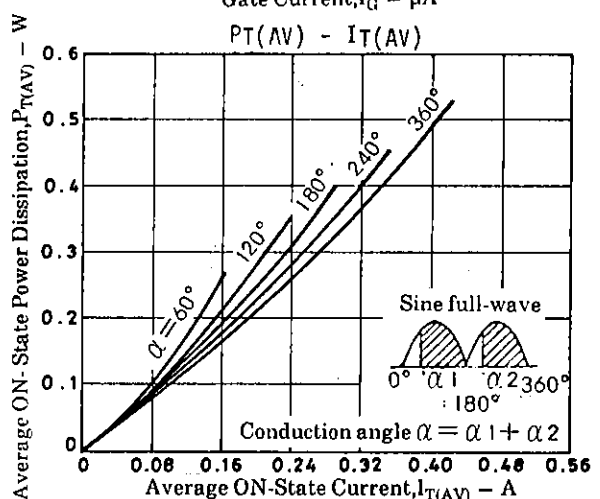
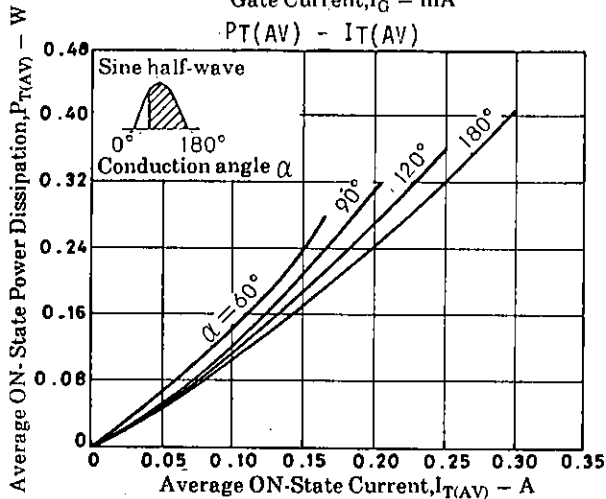
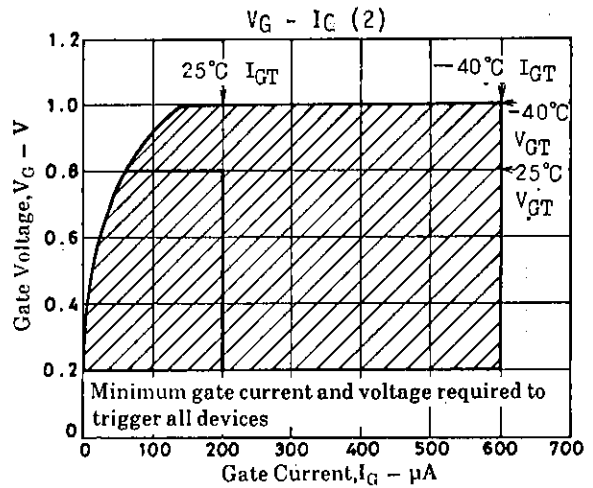
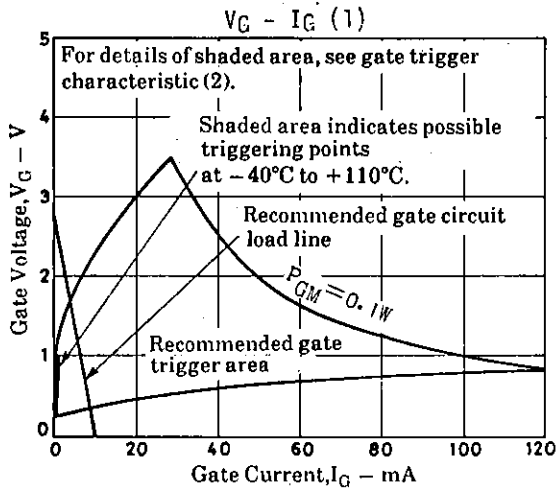
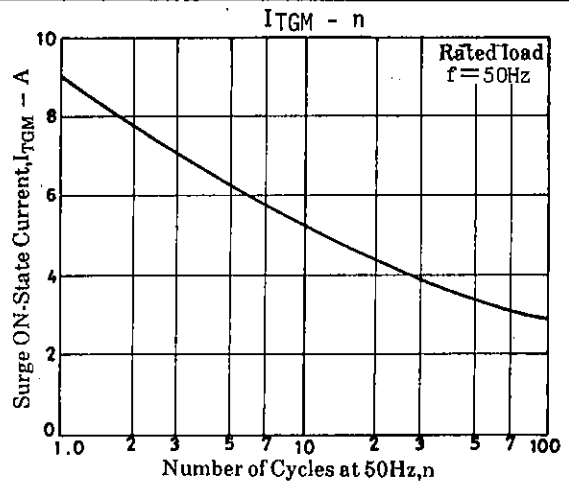
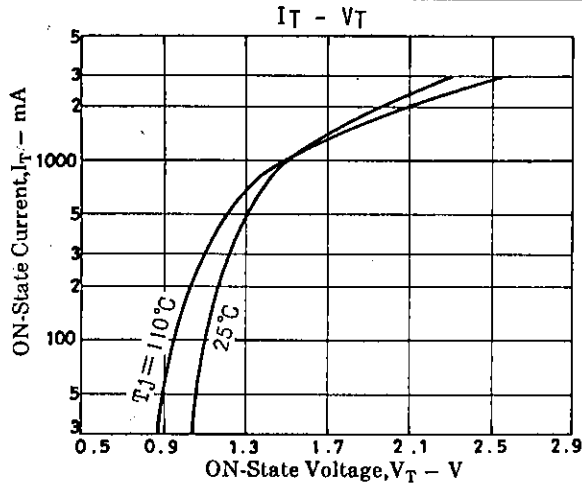
			min	typ	max	unit
Repetitive Peak OFF-State Current	$I_{DRM}$	Tj = 110°C, $V_D = V_{DRM}, R_{GK} = 1k\Omega$			0.1	mA
Repetitive Peak Reverse Current	$I_{RRM}$	Tj = 110°C, $V_D = V_{RRM}, R_{GK} = 1k\Omega$			0.1	mA
ON-State Voltage	$V_T$	$I_T = 2A$			2.0	V
Holding Current	$I_H$	$R_L = 100\Omega, R_{GK} = 1k\Omega$		4.0		mA
Gate Trigger Current	$I_{GT}$	$V_D = 6V, R_L = 100\Omega, R_{GK} = 1k\Omega$			0.2	mA
Gate Trigger Voltage	$V_{GT}$	$V_D = 6V, R_L = 100\Omega, R_{GK} = 1k\Omega$			0.8	V
Gate Nontrigger Voltage	$V_{GD}$	Ta = 110°C, $V_D = 6V, R_{GK} = 1k\Omega$	0.2			V
Thermal Resistance	$R_{th(j-c)}$				250	°C/W

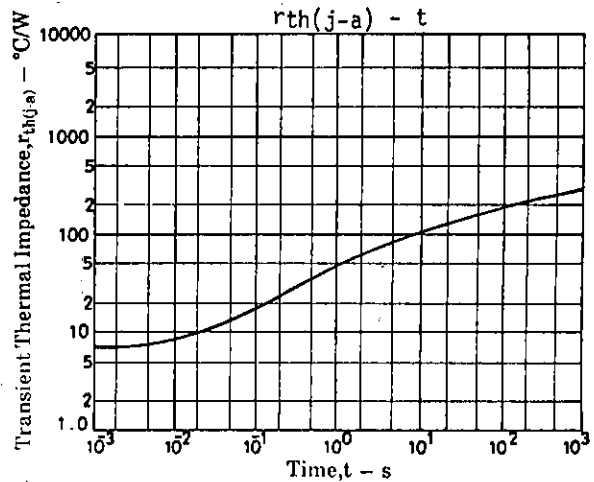
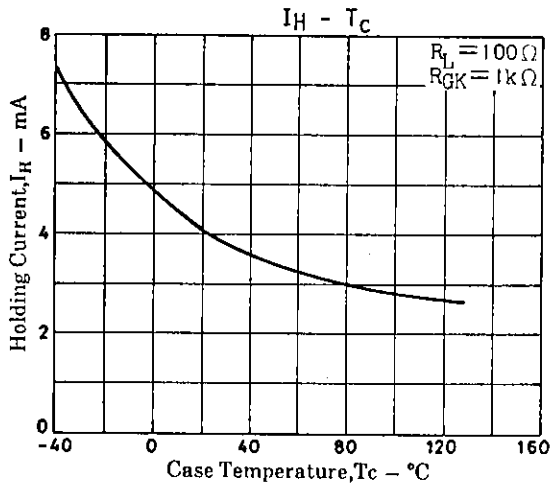
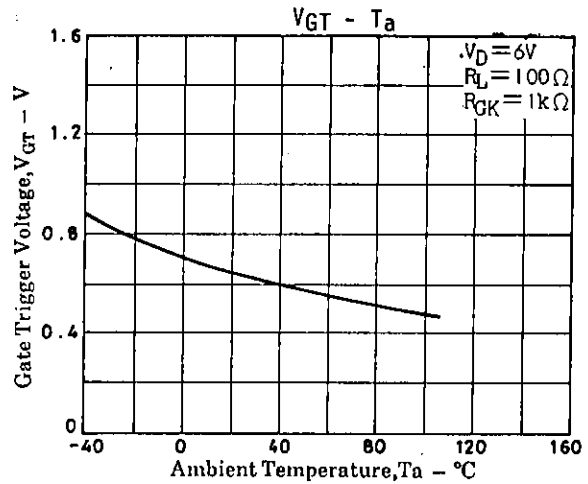
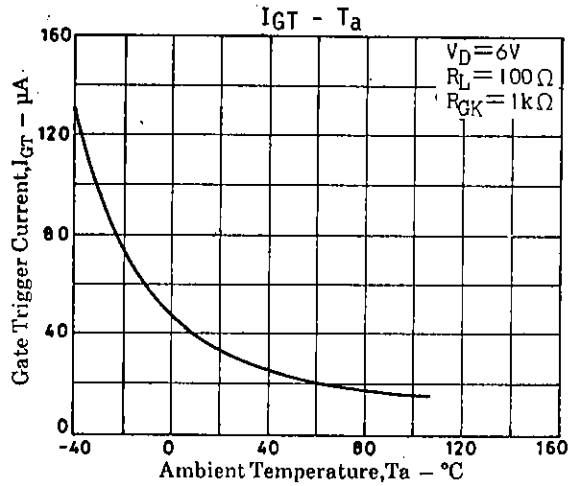
**Package Dimensions 1096A**  
(unit: mm)



C: Cathode  
A: Anode  
G: Gate

# DRA03T





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